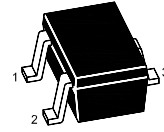


MMBTSC4082W

NPN Silicon Epitaxial Planar Transistor

High frequency application
TV Tuner, VHF oscillator applications.



1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	15	V
Emitter Base Voltage	V_{EBO}	3	V
Collector Current	I_C	50	mA
Base Current	I_B	25	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 3\text{ V}$, $I_C = 8\text{ mA}$	h_{FE}	40	200	-
Collector Base Cutoff Current at $V_{CB} = 15\text{ V}$	I_{CBO}	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 3\text{ V}$	I_{EBO}	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	30	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	15	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	3	-	V
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$	$V_{CE(sat)}$	-	0.5	V
Gain Bandwidth Product at $V_{CE} = 10\text{ V}$, $I_C = 8\text{ mA}$	f_T	650	-	MHz
Collector Base Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{CBO}	-	1.3	pF

